

N-Type 4H-SiC 6 inch Wafer



Grade	Production Grade	Research Grade	Dummy Grade
Diameter	150.0 mm ± 0.25 mm		
Surface Orientation	4.0° toward <11 $\bar{2}$ 0> ± 0.5°		
Primary Flat Orientation	{10 $\bar{1}$ 0} ± 5.0°		
Secondary Flat Orientation	None		
Primary Flat Length	47.5 mm ± 2.0 mm		
Secondary Flat Length	None		
Micropipe Densities	≤ 1 cm ⁻²	≤ 5 cm ⁻²	≤ 50 cm ⁻²
Resistivity	0.015-0.028 Ω•cm		≤ 0.03 Ω•cm
Foreign Polytypes	0		≤ 15%
Thickness	350.0 μm ± 25.0 μm or 500.0 μm ± 25.0 μm		
TTV	≤ 15μm		≤ 20μm
Bow	≤ 40μm		≤ 60μm
Warp	≤ 60μm		
Surface Roughness	CMP Si Face Ra < 0.3 nm (10 μm × 10 μm)		CMP Si Face Ra < 0.5 nm (10 μm × 10 μm)
Edge Chips/Indents by Diffuse Lighting	None permitted	Qty.2 <1.0mm width & depth	